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OFFICIAL

Docket No.: 21737-00013-US
(PATENT)

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Dated: 11/26/03

Signature:

(Deborah A. Belch)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:
Katsuki Hazama et al.

Application No.: 09/438,295

Art Unit: 2131

Filed: November 12, 1999

Examiner: Ly Hua

For: MULTILEVEL SEMICONDUCTOR MEMORY
WRITE/ READ METHOD
THERETO/THEREFROM AND STORAGE
MEDIUM STORING WRITE/READ PRO-GRAM

AMENDMENT IN RESPONSE TO NON-FINAL OFFICE ACTION

MS Non-Fee Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

INTRODUCTORY COMMENTS

In response to the Office Action dated August 21, 2003 (Paper No. 4), please amend the
above-identified U.S. patent application as follows:

Amendments to the Claims are reflected in the listing of claims which begins on page 2
of this paper.

Remarks/Arguments begin on page 18 of this paper.